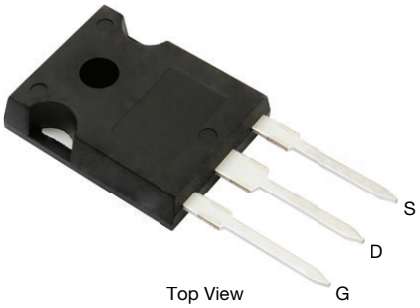
N-Channel 150 V (D-S) 175 °C MOSFET

TO-247



Top View

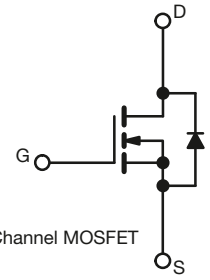
FEATURES

- ThunderFET® power MOSFET
- Low R_{DS} - Q_g figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Synchronous rectification
- Power supplies
- DC/AC inverter
- DC/DC converter
- Solar micro inverter
- Motor drive switch



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	150
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0054
$R_{DS(on)}$ max. (Ω) at V_{GS} = 7.5 V	0.0060
Q_g typ. (nC)	110
I_D (A)	100 [d]
Configuration	Single

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free and halogen-free	SUG80050E-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	150	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C	I_D	100 [d]	A
	T_C = 125 °C		100 [d]	
Pulsed drain current (t = 100 µs)		I_{DM}	300	
Continuous source-drain diode current		I_S	100 [d]	
Single pulse avalanche current [a]	L = 0.1 mH	I_{AS}	100	
Single pulse avalanche energy [a]		E_{AS}	500	mJ
Maximum power dissipation	T_C = 25 °C	P_D	500 [b]	W
	T_C = 125 °C		167 [b]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) [c]		R_{thJA}	40	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	0.3	

Notes

a. Duty cycle ≤ 1 %
b. See SOA curve for voltage derating
c. When mounted on 1" square PCB (FR4 material)
d. Package limited

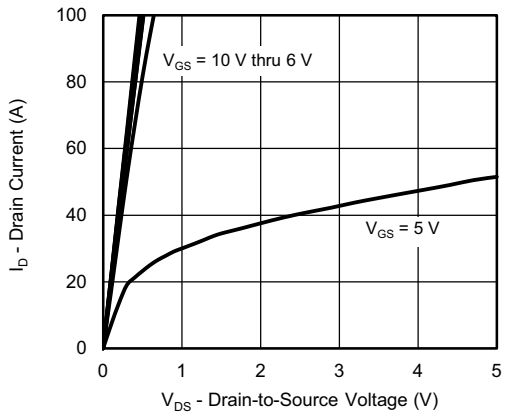
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	150	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2	-	4	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	250	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 150 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 150 V, V_{GS} = 0 V, T_J = 125 °C	-	-	150	
		V_{DS} = 150 V, V_{GS} = 0 V, T_J = 175 °C	-	-	5	mA
On-state drain current [a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	30	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A	-	0.0045	0.0054	Ω
		V_{GS} = 7.5 V, I_D = 15 A	-	0.0050	0.0063	
Forward transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A	-	60	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz	-	6250	-	pF
Output capacitance	C_{oss}		-	1100	-	
Reverse transfer capacitance	C_{rss}		-	65	-	
Total gate charge	Q_g	V_{DS} = 75 V, V_{GS} =10 V, I_D = 20 A	-	110	165	nC
Gate-source charge	Q_{gs}		-	33	-	
Gate-drain charge	Q_{gd}		-	28	-	
Gate resistance	R_g	f = 1 MHz	0.6	3.1	6.2	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = 75 V, R_L = 5 Ω, I_D ≅ 15 A, V_{GEN} = 10 V, R_g = 1 Ω	-	18	27	ns
Rise time	t_r		-	44	66	
Turn-off delay time	$t_{d(off)}$		-	72	108	
Fall time	t_f		-	55	83	
Drain-Source Body Diode Characteristics						
Pulse diode forward current (t = 100 µs)	I_{SM}		-	-	100	A
Body diode voltage	V_{SD}	I_F = 15 A, V_{GS} = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t_{rr}	I_F = 15 A, dI/dt = 100 A/µs	-	130	195	ns
Body diode reverse recovery charge	Q_{rr}		-	0.71	1.07	µC
Reverse recovery fall time	t_a		-	97	-	ns
Reverse recovery rise time	t_b		-	33	-	
Body diode peak reverse recovery charge	$I_{RM(REC)}$		-	12	18	A

Notes

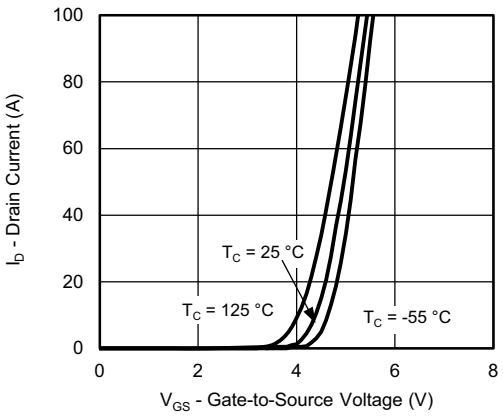
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

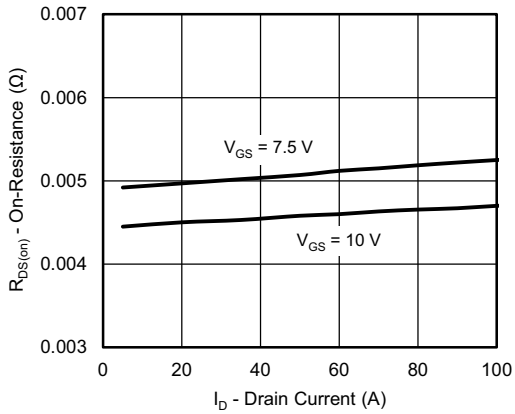
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



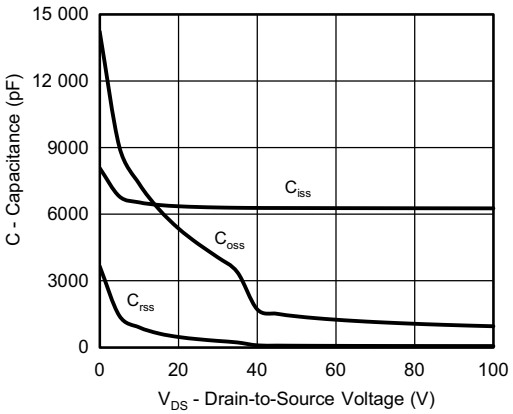
Output Characteristics



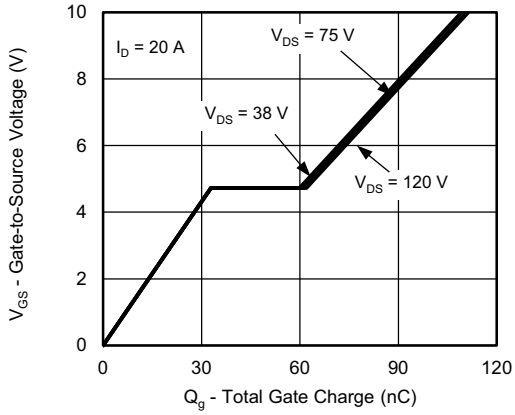
Transfer Characteristics



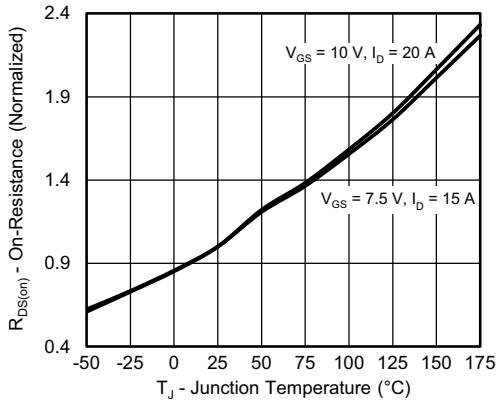
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

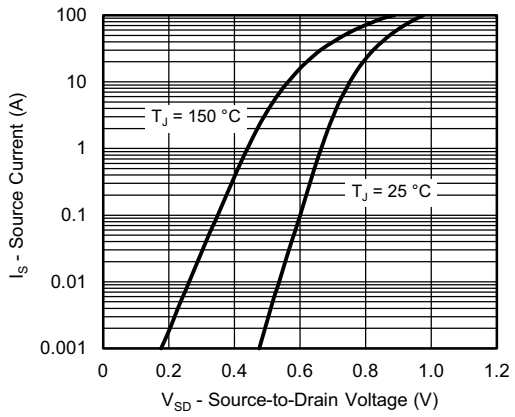


Gate Charge

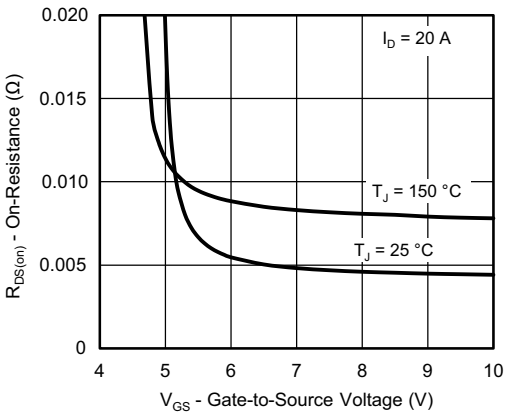


On-Resistance vs. Junction Temperature

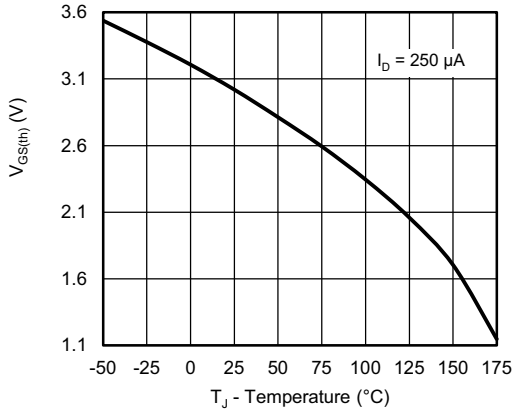
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



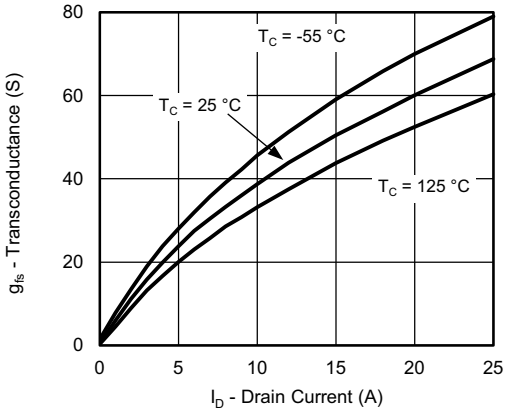
Source-Drain Diode Forward Voltage



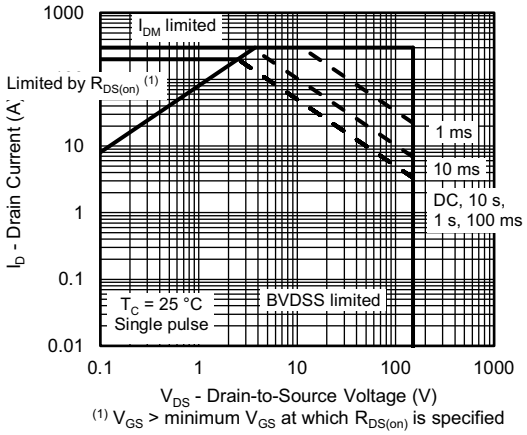
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

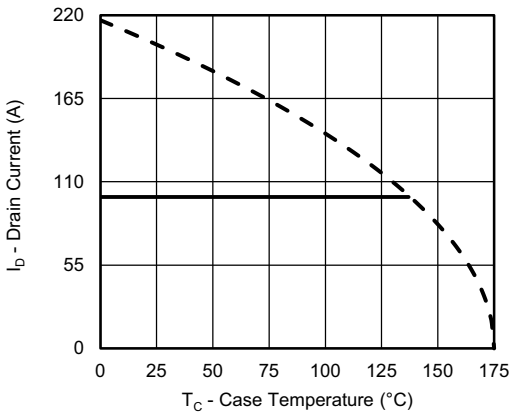


Transconductance

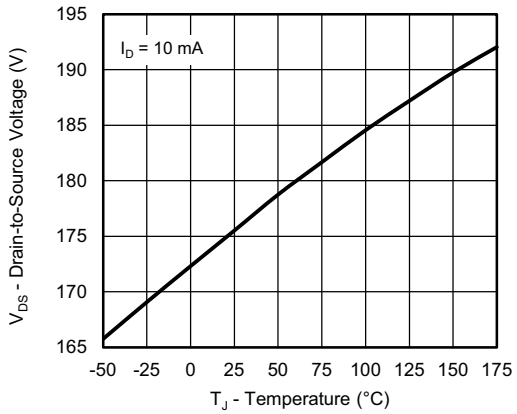


Safe Operating Area, Junction-to-Ambient

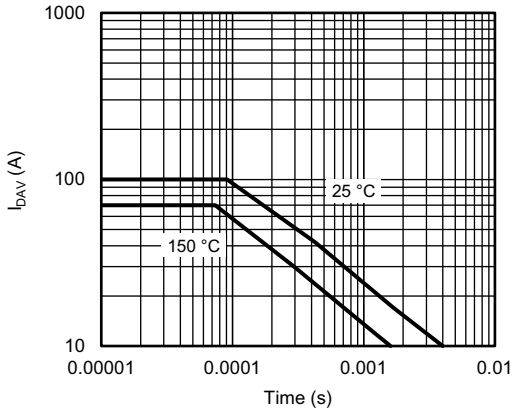
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Drain Source Breakdown vs. Junction Temperature

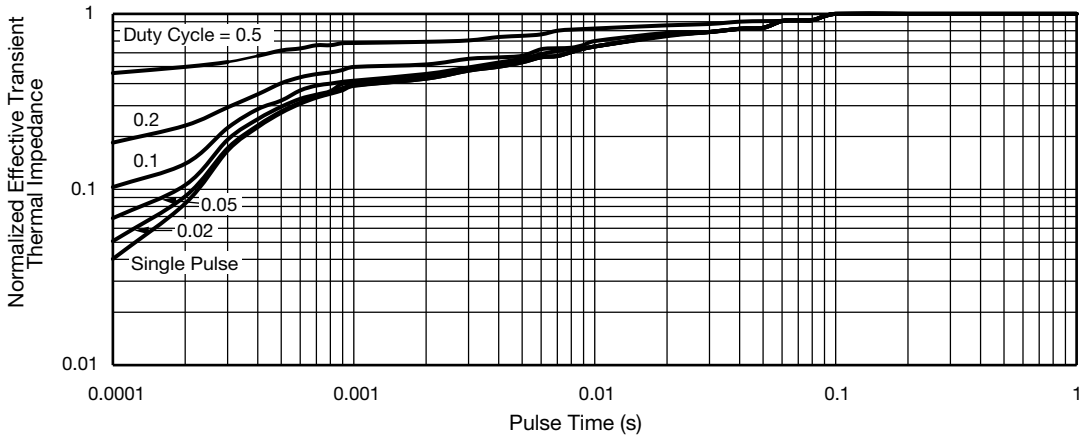


I_{DAV} vs. Time

Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

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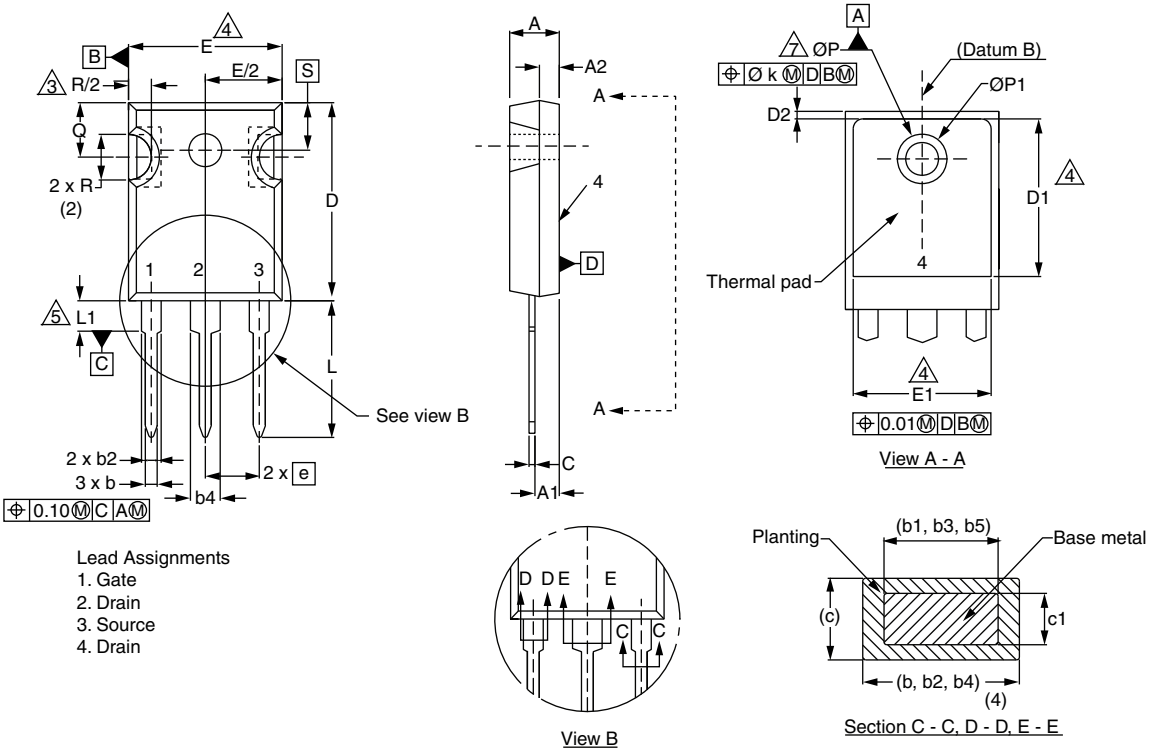
TO-247AC (High Voltage)



Lead Assignments
1. Gate
2. Drain
3. Source
4. Drain

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: X13-0103-Rev. D, 01-Jul-13
DWG: 5971

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.

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